PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: O77191

Koichi OHTO, et al.

Allowed: February 9, 2007

Appln. No.: 10/650,193

Group Art Unit: 2826

Confirmation No.: 6245

Examiner: Alexander O. WILLIAMS

Filed: August 28, 2003

For: SEMICONDUCTOR DEVICE HAVING SILICON-DIFFUSED METAL WIRING LAYER AND ITS MANUFACTURING METHOD

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP ISSUE FEE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby

notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached

PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem

material to patentability of the claims of the above-identified application.

- Japanese Patent Application Publication No. 2003-347299, published December 5, 2003, with English Abstract.
- Japanese Patent Application Publication No. 2001-291720 published October 19, 2001, with English Abstract.
- Japanese Patent Application Publication No. 2000-150517, published May 30, 2000, with English Abstract.
- Japanese Patent Application Publication No. 2000-058544, published February 25, 2000, with English Abstract.

- Japanese Patent Application Publication No. 11-186273, published July 9, 1999, with English Abstract.
- Japanese Patent Application Publication No. 06-177128, published June 24, 1994, with English Abstract.
- Japanese Patent Application Publication No. 2000-349085, published December 15, 2000, with English Abstract.
- Japanese Patent Application Publication No. 03-262125, published November 21, 1991, with English Abstract.
- Japanese Patent Application Publication No. 11-204523, published July 30, 1999, with English Abstract.

One copy of each of the listed documents is submitted herewith.

The present Information Disclosure Statement is being filed after either a Final Office Action, Notice of Allowance, or an action that otherwise closes prosecution in the application (whichever is earlier), but before payment of the Issue Fee, and therefore Applicant is submitting herewith a the fee of \$180.00 via EFS payment screen under 37 C.F.R. § 1.17(p), and a Statement Under 37 C.F.R. § 1.97(c).

The present information Disclosure Statement is being filed thirty days or fewer from the communication from a foreign patent office and a Statement Under 37 C.F.R. §1.704(d) is attached.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant encloses here with a copy of a corresponding Japanese Office Action dated February 14, 2007, and an English translation of the pertinent portions thereof which cites such documents and indicates the degree of relevance found by the foreign office.

INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 10/650,193

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The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a connectent reference against the claims of the present application.

The statutory fee of \$180,00 is being charged to Deposit Account No. 19-4880 via EFS

Payment Screen. The USPTO is also directed and authorized to charge all required fees, except

for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit

any overpayments to said Deposit Account.

Registration No. 25

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23373

Date: March 14, 2007

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Filed: August 28, 2003

FOI: SEMICONDUCTOR DEVICE HAVING SILICON-DIFFUSED METAL WIRING
LAYER AND ITS MANUFACTURING METHOD

STATEMENT UNDER 37 C.F.R. § 1,704(d)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The undersigned hereby states, upon information and belief:

That each item of information contained in the Information Disclosure Statement filed concurrently herewith was cited in a communication from a foreign patent office in a counterpart

foreign application, and that the communication was not received by any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filling of said Information Disclosure

Statement.

Respectfully submitted,

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Date: March 14, 2007

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STATEMENT UNDER 37 C.F.R. § 1.97(e)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The undersigned hereby states, upon information and belief:

That each item of information contained in the Information Disclosure Statement filed concurrently herewith was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of said Information Disclosure Statement.

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Date: March 14, 20007

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		JP CCCC			A		12-15-2003		Renesas Technolo	ery Comp	+
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		JP	2000-150517		A		05-30-2000		Hitachi Ltd.		-
		JP .	2000-058544		A		02-25-2000		Matsushita Electr	on Corp	
		JP	11-186273		A		07-09-1999		Ricoh Co Ltd		
		JP	06-17712		Α		06-24-199		Japan Energy Cor	p .	
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Substitute for Form 1449 A & B/PTO

*EXAMINER: Initial of reference considered, whether or not clintion in in confirmmence with MFEP 689. Draw line through eliminan if not in confirmmence and not considered. Include copy of this form with next communication to applicant.

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